

Silicon PNP Power Transistors

2SB536

DESCRIPTION

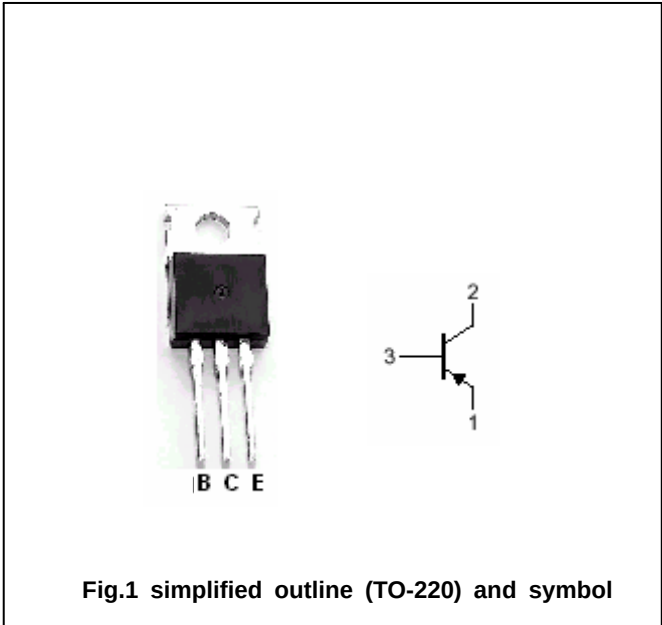
- With TO-220C package
- Complement to type 2SD381
- Low collector saturation voltage

APPLICATIONS

- Audio frequency power amplifier
- Low speed power switching

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-130	V
V _{CEO}	Collector-emitter voltage	Open base	-120	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-1.5	A
I _{CM}	Collector current-peak		-3.0	A
I _B	Base current		-0.3	A
P _T	Total power dissipation	T _a =25°C	1.5	W
		T _C =25°C	20	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-50~150	°C

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-10mA; I_B=0$	-120			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-1A; I_B=-0.1A$			-2.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-1A; I_B=-0.1A$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-120V; I_E=0$			-1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-3V; I_C=0$			-1.0	μA
h_{FE-1}	DC current gain	$I_C=-5mA; V_{CE}=-5V$	25			
h_{FE-2}	DC current gain	$I_C=-0.3A; V_{CE}=-5V$	40		250	
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-10V; f=1MHz$		35		pF
f_T	Transition frequency	$I_C=-0.1A; V_{CE}=-5V$		40		MHz

◆ h_{FE-2} Classifications

N	M	L	K
40-80	60-120	80-160	120-250

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PACKAGE OUTLINE

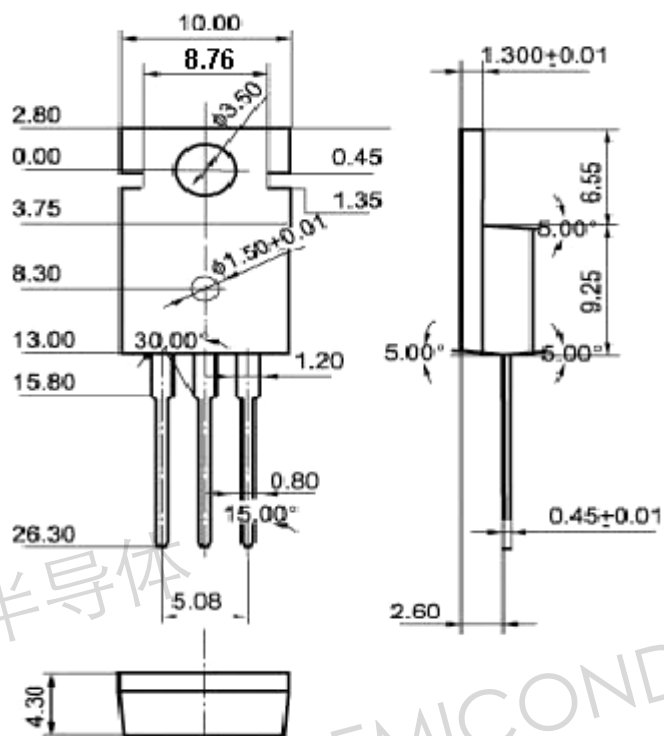


Fig.2 Outline dimensions (unindicated tolerance: $\pm 0.10\text{mm}$)